FINAL EXAMINATION - SOLUTIONS

(Average = 100, High = 120, and Low = 69)

Problem 1 - (20 points - This problem is required)

If the folded-cascode op amp shown having a small-signal voltage gain of 7464V/V is used as a comparator, find the dominant pole if $C_L = 5$ pF. If the input step is 10mV, determine whether the response is linear or slewing and find the propagation delay time. Assume the parameters of the NMOS transistors are K_N '=110V/ μ A², $V_{TN} = 0.7$ V, $\lambda_N = 0.04$ V⁻¹ and for the PMOS transistors are K_P '=110V/ μ A², $V_{TP} = -0.7$ V, $\lambda_P = 0.05$ V⁻¹.



Solution

 V_{OH} and V_{OL} can be found from many approaches. The easiest is simply to assume that V_{OH} and V_{OL} are 2.5V and -2.5V, respectively. However, no matter what the input, the values of V_{OH} and V_{OL} will be in the following range,

$$(V_{DD}-2V_{ON}) < V_{OH} < V_{DD}$$
 and $V_{DD} < V_{OH} < (V_{SS}+2V_{ON})$

The reasoning is as follows, suppose $V_{in} > 0$. This gives $I_1 > I_2$ which gives $I_6 < I_7$ which gives $I_9 < I_7$. V_{out} will increase until I_7 equals I_9 . The only way this can happen is for M5 and M7 to leave saturation. The same reasoning holds for $V_{in} < 0$.

Therefore assuming that V_{OH} and V_{OL} are 2.5V and -2.5V, respectively, we get

$$V_{in}(\min) = \frac{5V}{7464} = 0.67 \text{mV} \rightarrow k = \frac{10 \text{mV}}{0.67 \text{mV}} = 14.93$$

Problem 1 – Continued

The folded-cascode op amp as a comparator can be modeled by a single dominant pole. This pole is found as,

$$\begin{split} p_1 &= \frac{1}{R_{out}C_L} \text{ where } R_{out} \approx g_{m9}r_{ds9}r_{ds11} \| [g_{m7}r_{ds7}(r_{ds2} \| r_{ds5})] \\ g_{m9} &= \sqrt{2 \cdot 75 \cdot 110 \cdot 36} = 771 \mu \text{S}, \ g_{ds9} = g_{ds11} = 75 \times 10^{-6} \cdot 0.04 = 3 \mu \text{S}, \ g_{ds2} = 50 \times 10^{-6} (0.04) = 2 \mu \text{S} \\ g_{m7} &= \sqrt{2 \cdot 75 \cdot 50 \cdot 80} = 775 \mu \text{S}, \ g_{ds5} = 125 \times 10^{-6} \cdot 0.05 = 6.25 \mu \text{S}, \ g_{ds7} = 50 \times 10^{-6} (0.05) = 3.75 \mu \text{S} \\ g_{m9}r_{ds9}r_{ds11} &= (771 \mu \text{S}) \left(\frac{1}{3 \mu \text{S}}\right) \left(\frac{1}{3 \mu \text{S}}\right) = 85.67 \text{M}\Omega \\ g_{m7}r_{ds7}(r_{ds2} \| r_{ds5} \approx (775 \mu \text{S}) \left(\frac{1}{3.75 \mu \text{S}}\right) \left(\frac{1}{2 \mu \text{S}} \| \frac{1}{6.25 \mu \text{S}}\right) = 25.05 \text{M}\Omega , \\ R_{out} \approx 85.67 \text{M}\Omega \| 25.05 \text{M}\Omega = 19.4 \text{M}\Omega \end{split}$$

The dominant pole is found as, $p_1 = \frac{1}{R_{out}C_L} = \frac{1}{19.4 \times 10^6 5 \text{pF}} = 10,318 \text{ rps}$

The time constant is $\tau_1 = 96.9 \mu s$.

For a dominant pole system, the step response is, $v_{out}(t) = A_{vd}(1-e^{-t/\tau_1})V_{in}$ The slope is the largest at t = 0. Evaluating this slope gives,

$$\frac{dv_{out}}{dt} = \frac{A_{vd}}{\tau_1} e^{-t/\tau_1} V_{in} \quad \text{For } t = 0, \text{ the slope is } \frac{A_{vd}}{\tau_1} V_{in} = \frac{7464}{96.9 \mu \text{s}} (10 \text{mV}) = 0.77 \text{V/}\mu \text{s}$$

The slew rate of this op amp/comparator is $SR = \frac{I_3}{C_L} = \frac{100\mu A}{5pF} = 20V/\mu s$

Therefore, the comparator does not slew and its propagation delay time is found from the linear response as,

$$t_P = \tau_1 \ln\left(\frac{2k}{2k-1}\right) = 96.9 \mu \text{s} \cdot \ln\left(\frac{2 \cdot 14.93}{2 \cdot 14.93 \cdot 1}\right) = (96.9 \mu \text{s})(0.0341) = \underline{3.3 \mu \text{s}}$$

Problem 2 - (20 points - This problem is required)

A comparator consists of an amplifier cascaded with a latch as shown below. The amplifier has voltage gain of 10V/V and $f_{-3dB} = 100$ MHz and the latch has a time constant of 10ns. The maximum and minimum voltage swings of the amplifier and latch are V_{OH} and V_{OL} . When should the latch be enabled after the application of a step input to the amplifier of $0.05(V_{OH}-V_{OL})$ to get minimum overall propagation time delay? What is the value of the minimum propagation time delay? It may useful to recall that the propagation time delay of

 $\left(\frac{V_{OH}-V_{OL}}{2v_{il}}\right)$ where v_{il} is the latch input (ΔV_i of the text). the latch is given as $t_p = \tau_L \ln t$



Solution

The solution is based on the figure shown. We note that,

 $v_{oa}(t) = 10[1-e^{-\omega_{-}3\text{dB}t}]0.05(V_{OH}-V_{OL}).$ If we define the input voltage to the latch as, $v_{il} = x \cdot (V_{OH} - V_{OL})$

then we can solve for t_1 and t_2 as follows:

$$x \cdot (V_{OH} - V_{OL}) = 10[1 - e^{-\omega - 3dBt_1}] 0.05(V_{OH} - x = 0.5[1 - e^{-\omega - 3dBt_1}]$$

 V_{OL}) -This gives,

$$t_1 = \frac{1}{\omega_{-3\mathrm{dB}}} \ln\left(\frac{1}{1-2x}\right)$$

From the propagation time delay of the latch we get.

$$t_{2} = \tau_{L} \ln\left(\frac{V_{OH} - V_{OL}}{2v_{il}}\right) = \tau_{L} \ln\left(\frac{1}{2x}\right)$$

$$\therefore \quad t_{p} = t_{1} + t_{2} = \frac{1}{\omega_{-3dB}} \ln\left(\frac{1}{1 - 2x}\right) + \tau_{L} \ln\left(\frac{1}{2x}\right) \quad \Rightarrow \frac{dt_{p}}{dx} = 0 \text{ gives } x = \frac{\pi}{1 + 2\pi} = 0.4313$$

$$t_{1} = \frac{10\text{ns}}{2\pi} \ln\left(1 + 2\pi\right) = 1.592\text{ns} \cdot 1.9856 = \underline{3.16\text{ns}} \text{ and } t_{2} = 10\text{ns} \ln\left(\frac{1 + 2\pi}{2\pi}\right) = 1.477\text{ns}$$

$$\therefore \quad t_{1} = t_{1} + t_{2} = 3.16\text{ns} + 1.477\text{ns} = 4.637\text{ns}$$

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$$t_p = t_1 + t_2 = 3.16$$
ns + 1.477ns = 4.637ns



Problem 3 - (20 points - This problem is optional)

If $R_1 = R_2$ of the circuit shown, find an expression for the small-signal output resistance R_{out} ignoring R_L . Repeat including the influence of R_L on the output resistance. Let $R_1=R_2$ and $R_L =$ $1k\Omega$, dc currents through M1 and M2 be $v_{IN} \circ$ $500\mu A$, $W_1/L_1 = 100\mu m/1\mu m$ and $W_2/L_2 = 200\mu m/1\mu m$. Find the value of R_{out} .

<u>Solution</u>

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The loop-gain for this network can be written from inspection as,

$$LG = \left(\frac{R_1}{R_1 + R_1}\right) \left(\frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2} + G_L}\right)$$

Therefore, since the output is shunt feedback we can solve for output resistance as,

$$R_{out} = \frac{r_{ds1} ||r_{ds2} ||R_L}{1 + \left(\frac{R_1}{R_1 + R_1}\right) \left(\frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2} + G_L}\right)}$$

Setting $G_L = 0$ ($R_L = \infty$) gives the output resistance not including the load resistor, R_L , as

$$R_{out} = \frac{r_{ds1} || r_{ds2}}{1 + \left(\frac{R_1}{R_1 + R_1}\right) \left(\frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2}}\right)}$$

Calculating the small-signal parameters gives,

$$g_{m1} = \sqrt{2 \cdot 110 \cdot 500 \cdot 100} = 3.316 \text{mS}, \ g_{m2} = \sqrt{2 \cdot 50 \cdot 500 \cdot 200} = 3.162 \text{mS}$$

$$r_{ds1} = \frac{10^6}{0.04 \cdot 500} = 50 \text{k}\Omega \text{ and } r_{ds2} = \frac{10^6}{0.05 \cdot 500} = 40 \text{k}\Omega$$

$$R_{out}(R_L = \infty) = \frac{50 \text{k}\Omega ||40 \text{k}\Omega}{1 + 0.5 \left(\frac{3316 + 3162}{25 + 20}\right)} = \frac{22.22 \text{k}\Omega}{72.98} = 304\Omega$$

$$R_{out}(R_L = 1 \text{k}\Omega) = \frac{50 \text{k}\Omega ||40 \text{k}\Omega ||1 \text{k}\Omega}{1 + 0.5 \left(\frac{3316 + 3162}{25 + 20 + 1000}\right)} = \frac{957\Omega}{4.0995} = \underline{233\Omega}$$

As usual, straight-forward small-signal models are faster, summing the currents at the output,

$$\begin{split} I_{out} = V_{out} \Big[\frac{1}{r_{ds1}} + \frac{1}{r_{ds2}} + \frac{1}{R_1 + R_2} + \frac{g_{m1} + g_{m2}}{2} + \frac{1}{R_L} \Big] \approx V_{out} \Big[\frac{1}{r_{ds1}} + \frac{1}{r_{ds2}} + \frac{g_{m1} + g_{m2}}{2} + \frac{1}{R_L} \Big] \\ \therefore \qquad R_{out} = \Big[\frac{1}{r_{ds1}} + \frac{1}{r_{ds2}} + \frac{g_{m1} + g_{m2}}{2} + \frac{1}{R_L} \Big]^{-1} = 304\Omega \ (R_L = \infty) \\ R_{out} = \underline{233\Omega} \ (R_L = 1k\Omega) \end{split}$$

(Principle: Feedback is a great concept tool but a terrible analysis tool.)



Problem 4 - (20 points - This problem is optional)

A current mirror load, CMOS differential amplifier is shown. The current in M5 is 100µA. Assume the parameters of the NMOS transistors are K_N ' =110V/ μ A², V_{TN} = 0.7V, λ_N =0.04V⁻¹ and for the PMOS transistors are K_P ' =110V/ μA^2 , V_{TP} = 0.7V, $\lambda_P = 0.04 V^{-1}$. (a.) Find the small-signal v_{in} output resistance and voltage gain if the W/L ratio of M1 and M2 is $100\mu m/1\mu m$. (b.) If the W/L + 0 ratio of M3 and M4 is 50μ m/1 μ m and C_{ox} = $24.7 \times 10^{-4} \text{F/m}^2$. and the effective output capacitance is 1pF, find all roots of this amplifier (ignore the influence of C_{gd4}). (c.) What is the -3dB frequency in Hertz?



<u>Solution</u>

The small-signal model suitable for this problem is shown below.

 $C_1 = 2(0.667)(50 \mathrm{x} 10^{-12} \mathrm{m}^2)(24.7 \mathrm{x} 10^{-4} \mathrm{F} / \mathrm{m}^2) = 0.1647 \mathrm{pF} \qquad g_{m3} = \sqrt{2 \cdot 50 \cdot 50 \cdot 50} = 500 \mu \mathrm{S}$

$$\begin{split} V_{out} &= (g_{m4}V_1 - g_{m2}V_{gs2})Z_{out} = \left(\frac{g_{m4}g_{m1}V_{gs1}}{g_{m3} + sC_1} - g_{m2}V_{gs2}\right)Z_{out} \\ &= \left[\left(\frac{1}{s\frac{C_1}{g_{m3}} + 1}\right)\left(\frac{g_{m1}V_{in}}{2}\right) - \frac{g_{m2}V_{in}}{2}\right]\left(\frac{1}{sC_L + g_{ds2} + g_{ds4}}\right) \\ &= -g_{md}\left(\frac{s\frac{C_1}{g_{m3}} + 2}{s\frac{C_1}{g_{m3}} + 1}\right)\left(\frac{1}{sC_2 + g_{ds2} + g_{ds4}}\right)\frac{V_{in}}{2} = -g_{md}\left(\frac{s\frac{C_1}{2g_{m3}} + 1}{s\frac{C_1}{g_{m3}} + 1}\right)\left(\frac{1}{sC_2 + g_{ds2} + g_{ds4}}\right)V_{in} \end{split}$$

The small-signal ourput resistance and voltage gain is,

$$R_{out} = \frac{1}{g_{ds2} + g_{ds4}} = \frac{10^6}{50 \ (0.05 + 0.04)} = \underline{222k\Omega} \qquad A_{vd} = -g_{m1}R_{out}$$

 $g_{m1} = g_{m1} = \sqrt{2 \cdot 110 \cdot 100 \cdot 50} = 1.049 \text{mS} \implies A_{vd} = -g_{m1}R_{out} = (1.049)(222) = -233 \text{V/V}$ The roots of this circuit are,

$$p_1 = -\frac{g_{m3}}{C_1} = -\frac{500\mu\text{S}}{0.1647\text{pF}} = -\frac{3.036\text{x}10^9\text{rps}}{0.1647\text{pF}}, z_1 = 2p_1 = -\frac{6.072\text{x}10^9\text{rps}}{0.1647\text{pF}},$$

and $p_2 = -\frac{g_{ds2} + g_{ds4}}{C_2} = -\frac{1}{222\text{k}\Omega \cdot 1\text{pF}} = -\frac{4.504\text{x}10^6\text{ rps}}{0.1647\text{pF}} \implies f_{-3\text{dB}} = -\frac{4.504\text{x}10^6}{2\pi} = -\frac{717\text{kHz}}{2\pi}$

Problem 5 - (20 points - This problem is optional)

The simplified schematic of a feedback amplifier is shown. Use the method of feedback analysis to find v_2/v_1 , $R_{in} = v_1/i_1$, and $R_{out} = v_2/i_2$. Assume that all transistors are matched and that $\beta = 100$, $r_{\pi} = 5k\Omega$ and $r_o = \infty$.



<u>Solution</u>

Open-loop, quasi-ac model:



Small-signal, open-loop model:



$$= (1+\beta)[R_{6}||(R_{2}+R_{4})]\left(\frac{-\beta R_{5}}{R_{5}+r_{\pi}+(1+\beta)[R_{6}||(R_{2}+R_{4})]}\right)\left(\frac{-\beta R_{3}}{R_{3}+r_{\pi}}\right)\left(\frac{1}{R_{i}}\right)$$

= [(101)(954.55)](-8.976)(-66.67)(1/101.19k\Omega) = 570.16 V/V
$$f = \frac{R_{2}}{R_{2}+R_{4}} = \frac{1}{21} = 0.0476 \text{ and } R_{0} = \frac{v_{0}'}{i_{2}'} = R_{6}||(R_{2}+R_{4})||\left(\frac{r_{\pi}+R_{5}}{1+\beta}\right) = 128.5\Omega$$

Closed-loop quantities are:

$$A_{vf} = \frac{v_0}{v_s} = \frac{a}{1+af} = \frac{570.16}{1+27.15} = 20.25, R_{if} = (1+af)R_i = 2.848M\Omega$$

$$\therefore \qquad R_{out} = R_{of} = \frac{R_0}{1+A_v\beta_f} = \frac{128.5\Omega}{28.15} = 4.565\Omega$$

$$R_{in} = R_1 + R_{if} = 2.858M\Omega \qquad \text{and} \qquad \frac{v_2}{v_1} = A_{vf} \frac{R_{if}}{R_1 + R_{if}} = 20.18 \text{ V/V}$$

Problem 6 - (20 points - This problem is optional)

A voltage follower feedback circuit is shown. For the MOS transistor, $I_D = 0.5$ mA, $K' = 180 \mu$ A/V², $r_{ds} = \infty$, and W/L =100. Although, the bulk effect, g_{mbs} , should be considered, for simplicity ignore the bulk effects in this problem. For the op amp, assume that $R_i = 1M\Omega$, $R_o = 10k\Omega$, and $a_v = 1000$. Calculate the input resistance and output resistance using Blackman's formula given below.



$$R_{out} = R_{out} \text{ (Controlled Source Gain=0)} \left[\frac{1 + RR(\text{output port shorted})}{1 + RR(\text{output port open})} \right]$$

Solution

Circuit for calculating the return ratios.



Input Port:

$$R_{in}(a_v=0) = R_i + (1/g_m),$$
 $g_m = \sqrt{2 \cdot 500 \cdot 100 \cdot 180} = 4.243 \text{mS}$
 $R_{in}(a_v=0) = 1M\Omega + 236\Omega \approx 1M\Omega$

RR(input port shorted):

$$V_r = -g_m R_i V_2 \text{ and } V_2 = a_v V_t - g_m R_i V_2 \longrightarrow V_r = \frac{-a_v g_m R_i}{1 + g_m R_i} V_t$$

$$RR(\text{input port shorted}) = -\frac{V_r}{V_t} = \frac{-a_v g_m R_i}{1 + g_m R_i} = -\frac{1000 \cdot 4.243 \text{mS} \cdot 1\text{M}\Omega}{1 + 4.243 \text{mS} \cdot 1\text{M}\Omega} = -999.8$$

$$RR(\text{input port open});$$

KR(input port open):

$$RR(\text{input port open}) = 0 \text{ because } V_r = 0$$

$$\therefore \qquad R_{in} = R_{in} (a_v = 0) \left[\frac{1 + RR(\text{output port shorted})}{1 + RR(\text{output port open})} \right] = 1M\Omega(1+999.8) = \underline{1000.8M\Omega}$$
Output Port:

С

 $R_{out}(a_v=0) = R_i \parallel (1/g_m) \approx 236\Omega$

RR(output port shorted):

$$RR($$
output port shorted $) = 0$ because $V_r = 0$

RR(output port open):

Same as the *RR* for the input port shorted.

$$\therefore \qquad R_{out} = R_{out} (a_v = 0) \left[\frac{1 + RR(\text{output port shorted})}{1 + RR(\text{output port open})} \right] = 236\Omega \left(\frac{1+0}{1+999.8} \right) = \underline{0.236\Omega}$$

Problem 7 - (20 points - This problem is optional)

A CMOS op amp capable of operating from 1.5V power supply is shown. All device lengths are 1µm and are to operate in the saturation region. Design all of the W values of every transistor of this op amp to meet the following specifications.

Slew rate = $\pm 10 V/\mu s$	$V_{out}(max) = 1.25V$	$V_{out}(min) = 0.75V$							
$V_{ic}(min) = 1V$	$V_{ic}(max) = 2V$	GB = 10MHz							
Phase margin = 60° when the output pole = 2GB and the RHP zero = 10GB.									
Keep the mirror pole ≥ 10 GB (C _{ox} = 0.5 fF/ μ m ²).									



 $\frac{1}{2}$ S02FEP7 Your design should meet or exceed these specifications. Ignore bulk effects in this problem and summarize your W values to the nearest micron, the value of $C_c(pF)$, and $I(\mu A)$ in the following table. Use the following model parameters: $K_N'=24\mu A/V^2$, $K_P'=8\mu A/V^2$, V_{TN} $= -V_{TP} = 0.75V$, $\lambda_N = 0.01V^{-1}$ and $\lambda_P = 0.02V^{-1}$.

<u>Solution</u>

$$\begin{array}{l} \hline 1.) & p_{2}=2GB \Rightarrow g_{m6}/C_{L}=2g_{m1}/C_{c} \text{ and } z=10GB \Rightarrow g_{m6}=10g_{m1}. \\ \therefore & \boxed{C_{c}=C_{L}/5=2pF} \\ \hline 2.) & I=C_{c}\cdot SR=(2x10^{-12})\cdot 10^{7}=20\mu A \\ \therefore & \boxed{I=20\mu A} \\ \hline 3.) & GB=g_{m1}/C_{c} \Rightarrow g_{m1}=20\pi x10^{6}\cdot 2x10^{-12}=40\pi x10^{-6}=125.67\mu S \\ & \frac{W_{1}}{L_{1}}=\frac{W_{2}}{L_{2}}=\frac{g_{m1}^{2}}{2K_{N}(I/2)}=\frac{(125.67x10^{-6})^{2}}{2\cdot 24x10^{-6}\cdot 10x10^{-6}}=32.9 \Rightarrow \boxed{W1=W_{2}=33\mu m} \\ \hline 4.) & V_{ic}(min)=V_{DS5}(sat.)+V_{GS1}(10\mu A)=1V \rightarrow V_{DS5}(sat.)=1-\sqrt{\frac{2\cdot10}{24\cdot33}} \cdot 0.75=0.0908 \\ & V_{DS5}(sat)=0.0908=\sqrt{\frac{2\cdot I}{K_{N}S_{5}}} \rightarrow W_{5}=\frac{2\cdot 20}{24\cdot (0.0908)^{2}}=201.9\mu m \\ \hline W_{5}=202\mu m \\ \hline 5.) & V_{ic}(max)=V_{DD}-V_{SD11}(sat)+V_{TN}=1.5-V_{SD11}(sat)+0.75=2V \rightarrow V_{SD11}(sat)=0.25V \\ & V_{SD11}(sat)\leq\sqrt{\frac{2\cdot1.5I}{K_{P}\cdot S_{11}}} \rightarrow S_{11}=W_{11}\geq \frac{2\cdot30}{(0.25)^{2}\cdot 8}=120 \rightarrow \underline{W_{11}=W_{12}\geq 120\mu m} \\ \end{array}$$

Problem 7 - Continued

6.) Choose $S_3(S_4)$ by satisfying $V_{ic}(max)$ specification then check mirror pole.

$$\begin{split} V_{ic}(\max) &\geq V_{GS3}(20\mu A) + V_{TN} \rightarrow V_{GS3}(20\mu A) = 1.25 V \geq \sqrt{\frac{2 \cdot I}{K_N \cdot S_3}} + 0.75 V \\ S_3 &= S_4 = \frac{2 \cdot 20}{(0.5)^2 \cdot 24} = 6.67 \implies \boxed{W_3 = W_4 = 7\mu m} \end{split}$$

7.) Check mirror pole ($p_3 = g_{m3}/C_{Mirror}$).

$$p_3 = \frac{g_{m3}}{C_{Mirror}} = \frac{g_{m3}}{2 \cdot 0.667 \cdot W_3 \cdot L_3 \cdot C_{ox}} = \frac{\sqrt{2 \cdot 24 \cdot 6.67 \cdot 20 \times 10^{-6}}}{2 \cdot 0.667 \cdot 6.67 \cdot 0.5 \times 10^{-15}} = 17.98 \times 10^{-6}$$

which is much greater than 10GB (0.0628×10^9). Therefore, W₃ and W₄ are OK.

8.)
$$g_{m6} = 10g_{m1} = 1256.7\mu S$$

a.) $g_{m6} = \sqrt{2K_NS_610I} \implies W_6 = 164.5\mu m$
b.) $V_{out}(min) = 0.5 \implies V_{DS6}(sat) = 0.5 = \sqrt{\frac{2 \cdot 10I}{K_NS_6}} \implies W_6 = 66.67\mu m$
Therefore, use $W_6 = 165\mu m$
Note: For proper mirroring, $S_4 = \frac{I_4}{I_6} S_6 = 8.25\mu m$ which is close enough to 7 μm .

9.) Use the $V_{out}(max)$ specification to design W_7 .

$$V_{out}(max) = 0.25V \ge V_{DS7}(sat) = \sqrt{\frac{2 \cdot 200 \mu A}{8 x 10^{-6} \cdot S_7}}$$

 $\therefore S_7 \ge \frac{400 \mu A}{8 x 10^{-6} (0.25)^2} \implies W_7 = 800 \mu m$

10.) Now to achieve the proper currents from the current source I gives,

 $S_9 = S_{10} = \frac{S_7}{10} = 80 \implies W_9 = W_{10} = 80 \mu m$

and

 $S_{11} = S_{12} = \frac{1.5 \cdot S_7}{10} = 120 \rightarrow W_{11} = W_{12} = 120 \mu m$. We saw in step 5 that W_{11} and W_{12} had to be greater than 120 μ m to satisfy $V_{ic}(max)$. \therefore $W_{11}=W_{12}=120\mu m$

11.)
$$P_{diss} = 15I \cdot 1.5V = 300 \mu A \cdot 1.5V = 450 \mu W$$

C_c	Ι	$W_1 = W_2$	$W_3 = W_4$	$W_5 = W_8$	W_6	W_7	$W_9 = W_{10}$	$W_{11} = W_{12}$	<i>P</i> _{diss}
2pF	20µA	33µm	7μm	202µm	165µm	800µm	80µm	120µm	450µW

Problem 8 – (20 points – This problem is optional)

A differential CMOS amplifier using depletion mode input devices is shown. Assume that the normal MOSFETs parameters are $K_N' = 110 \text{V}/\mu \text{A}^2$, $V_{TN} =$ 0.7V, $\lambda_N = 0.04 \text{V}^{-1}$ and for the PMOS transistors are K_P ' =110V/ μA^2 , $V_{TP} = 0.7$ V, $\lambda_P = 0.04$ V⁻¹. For the depletion mode NMOS transistors, the parameters are the same as the normal NMOS except that $V_{TN} = -0.5$ V. (a.) What is the maximum input common-mode voltage, (b.) What is the minimum input $V_{icm}^+(\max)?$ common-mode voltage, V_{icm} (min)? (c.) What value of V_{DD} gives an $ICMR = 0.5V_{DD}$?



<u>Solution</u>

(a.)
$$V_{icm}^{+}(\max) = V_{DD} - V_{SD3}(\operatorname{sat}) - V_{DS1}(\operatorname{sat}) + V_{GS1}(50\mu\text{A})$$

 $i_D = \frac{\beta}{2} (V_{GS1} - V_{T1})^2 \rightarrow V_{GS1} = \sqrt{\frac{2i_D}{\beta}} + V_{T1} = V_{DS1}(\operatorname{sat}) + V_{T1}$
 $\therefore V_{icm}^{+}(\max) = V_{DD} - V_{SD3}(\operatorname{sat}) + V_{T1} = V_{DD} - \sqrt{\frac{2I_{D3}}{\beta_3}} + V_{T1}$
 $V_{icm}^{+}(\max) = V_{DD} - 0.4472 - 0.5 = \underline{V_{DD}} - 0.9472$
(b.) $V_{icm}^{-}(\min) = V_{DS5}(\operatorname{sat}) + V_{GS1}(50\mu\text{A}) = V_{DS5}(\operatorname{sat}) + V_{DS1}(\operatorname{sat}) + V_{T1}$
 $V_{icm}^{-}(\min) = \sqrt{\frac{2I_{D5}}{\beta_5}} + \sqrt{\frac{2I_{D1}}{\beta_1}} + V_{T1} = 0.1348 + 0.0953 - 0.5 = \underline{-0.2698V}$

(c.)
$$ICMR = V_{icm}^{+}(\max) - V_{icm}^{-}(\min) = V_{DD} - 0.9472 + 0.2698 = V_{DD} - 0.6774$$

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$$V_{DD} - 0.6774 = 0.5V_{DD} \rightarrow V_{DD} = 2(0.6774) = 1.355V_{DD}$$